

MOSFETs Silicon N-channel MOS (U-MOSVII-H)

# TPW4R50ANH

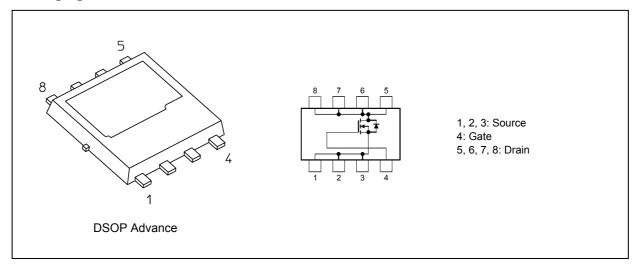
#### 1. Applications

- DC-DC Converters
- Switching Voltage Regulators
- · Motor Drivers

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 22 \text{ nC (typ.)}$
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 3.7 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (4) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 100 \text{ V)}$
- (5) Enhancement mode:  $V_{th} = 2.0$  to 4.0 V ( $V_{DS} = 10$  V,  $I_D = 1.0$  mA)

#### 3. Packaging and Internal Circuit





#### 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteristics                |                        |                    | Symbol           | Rating     | Unit |
|--------------------------------|------------------------|--------------------|------------------|------------|------|
| Drain-source voltage           |                        |                    | $V_{DSS}$        | 100        | V    |
| Gate-source voltage            |                        |                    | $V_{GSS}$        | ±20        |      |
| Drain current (DC)             | $(T_c = 25 ^{\circ}C)$ | (Note 1), (Note 2) | Ι <sub>D</sub>   | 92         | Α    |
| Drain current (pulsed)         | (t = 100 μs)           | (Note 1)           | $I_{DP}$         | 400        | Α    |
| Power dissipation              | $(T_c = 25 ^{\circ}C)$ |                    | $P_D$            | 142        | W    |
| Power dissipation              |                        | (Note 3)           | $P_D$            | 2.5        | W    |
| Power dissipation              |                        | (Note 4)           | $P_D$            | 0.8        | W    |
| Single-pulse avalanche energy  |                        | (Note 5)           | E <sub>AS</sub>  | 125        | mJ   |
| Single-pulse avalanche current |                        | (Note 5)           | I <sub>AS</sub>  | 92         | Α    |
| Channel temperature            |                        |                    | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature            |                        |                    | T <sub>stg</sub> | -55 to 150 | °C   |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Characteristic                        | Symbol                                 | Max      | Unit                  |      |      |
|---------------------------------------|--|----------|-----------------------|------|------|
| Channel-to-case thermal resistance    | Bottom Drain $(T_c = 25 ^{\circ}C)$    |          | R <sub>th(ch-c)</sub> | 0.88 | °C/W |
| Channel-to-case thermal resistance    | Top Source<br>(T <sub>c</sub> = 25 °C) |          | R <sub>th(ch-c)</sub> | 0.93 | °C/W |
| Channel-to-ambient thermal resistance | (T <sub>a</sub> = 25 °C)               | (Note 3) | R <sub>th(ch-a)</sub> | 50   | °C/W |
| Channel-to-ambient thermal resistance | (T <sub>a</sub> = 25 °C)               | (Note 4) | R <sub>th(ch-a)</sub> | 156  | °C/W |

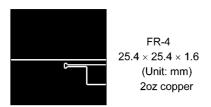
Note 1: Ensure that the channel temperature does not exceed 150 °C.

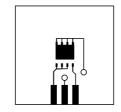
Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5:  $V_{DD}$  = 60 V,  $T_{ch}$  = 25 °C (initial), L = 16  $\mu$ H,  $I_{AS}$  = 92 A





FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

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### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                    | Min | Тур. | Max  | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _   | _    | ±0.1 | μА   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V    | _   | _    | 10   |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 100 | _    | _    | V    |
|                                | V <sub>(BR)DSX</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V   | 65  | _    | _    |      |
| Gate threshold voltage         | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA   | 2.0 | _    | 4.0  |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 46 A     | _   | 3.7  | 4.5  | mΩ   |

#### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max  | Unit |
|--------------------------------|------------------|--|-----|------|------|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 4000 | 5200 | pF   |
| Reverse transfer capacitance   | $C_{rss}$        |  | _   | 31   | 63   |      |
| Output capacitance             | C <sub>oss</sub> |  | _   | 700  | _    |      |
| Gate resistance                | r <sub>g</sub>   | _  | _   | 1.0  | 1.5  | Ω    |
| Switching time (rise time)     | t <sub>r</sub>   | See Fig. 6.2.1   | _   | 9.6  | _    | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  | _   | 25   | _    |      |
| Switching time (fall time)     | t <sub>f</sub>   |  | _   | 13   | _    |      |
| Switching time (turn-off time) | t <sub>off</sub> |  |     | 52   |      |      |

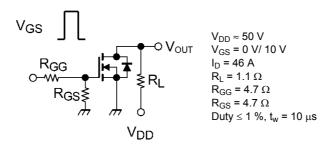


Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_{g}$          | $V_{DD} \approx 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 46 \text{ A}$ | _   | 58   | _   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |  | _   | 22   | _   |      |
| Gate-drain charge                               | $Q_{gd}$         |  | _   | 12   | _   |      |
| Gate switch charge                              | Q <sub>SW</sub>  |  | _   | 22   | _   |      |

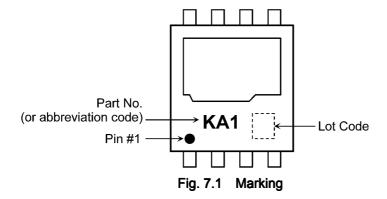
#### 6.4. Source-Drain Characteristics (Ta = 25 °C unless otherwise specified)

| Characteristics                         | Symbol                           | Test Condition   | Min | Тур. | Max  | Unit |
|---|----------------------------------|--|-----|------|------|------|
| Reverse drain current (pulsed) (Note 6) | I <sub>DRP</sub><br>(t = 100 μs) | _  | _   | _    | 400  | Α    |
| Diode forward voltage                   | $V_{DSF}$                        | I <sub>DR</sub> = 92 A, V <sub>GS</sub> = 0 V              |     |      | -1.2 | V    |
| Reverse recovery time                   | t <sub>rr</sub>                  | V <sub>R</sub> = 50 V, I <sub>DR</sub> = 23 A,             | _   | 63   |      | ns   |
| Reverse recovery charge                 | $Q_{rr}$                         | $V_{GS} = 0 \text{ V}, -dI/dt = 100 \text{ A}/\mu\text{s}$ |     | 104  |      | nC   |

Note 6: Ensure that the channel temperature does not exceed 150 °C.



### 7. Marking



#### 8. Characteristics Curves (Note)

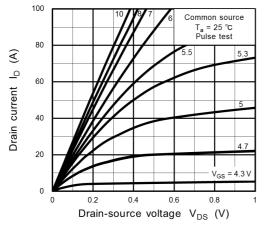
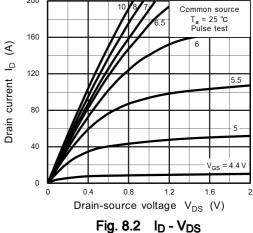


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>



200

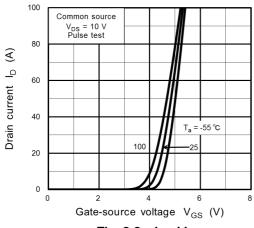


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

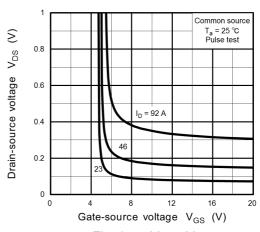


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

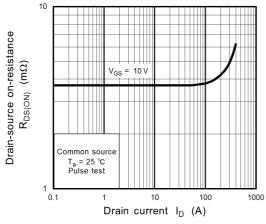


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

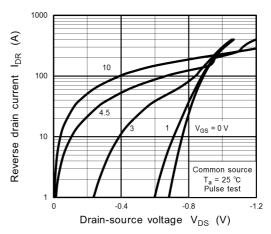


Fig. 8.6 IDR - VDS

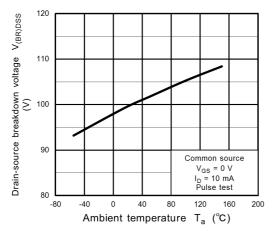


Fig. 8.7 V<sub>(BR)DSS</sub> - T<sub>a</sub>

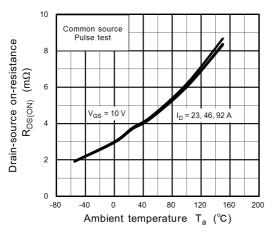


Fig. 8.9 R<sub>DS(ON)</sub> - T<sub>a</sub>

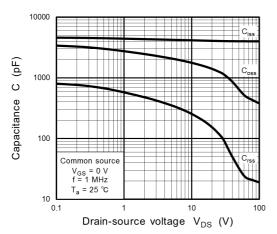


Fig. 8.11 Capacitance - V<sub>DS</sub>

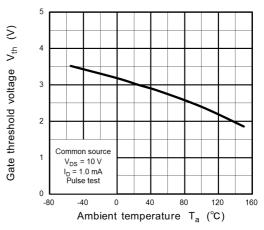


Fig. 8.8 V<sub>th</sub> - T<sub>a</sub>

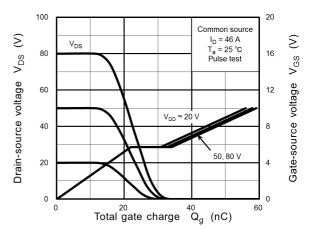


Fig. 8.10 Dynamic Input/Output Characteristics

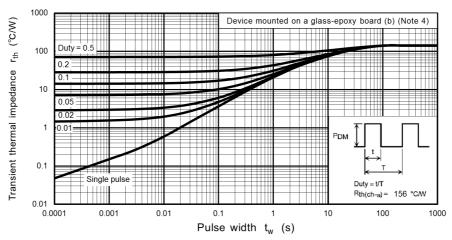


Fig. 8.12 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

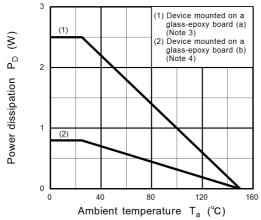


Fig. 8.13 P<sub>D</sub> - T<sub>a</sub> (Guaranteed Maximum)

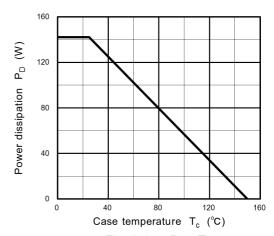


Fig. 8.14 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

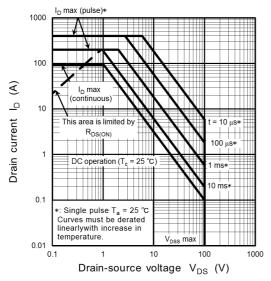


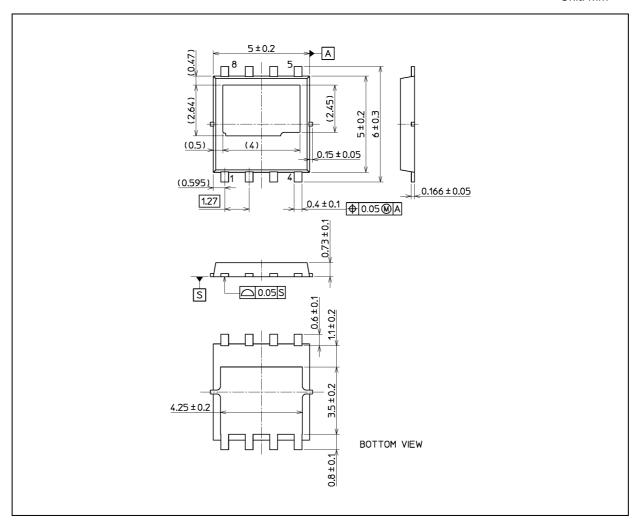
Fig. 8.15 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 0.098 g (typ.)

| Package Name(s)        |
|------------------------|
| TOSHIBA: 2-5S1A        |
| Nickname: DSOP Advance |



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